

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

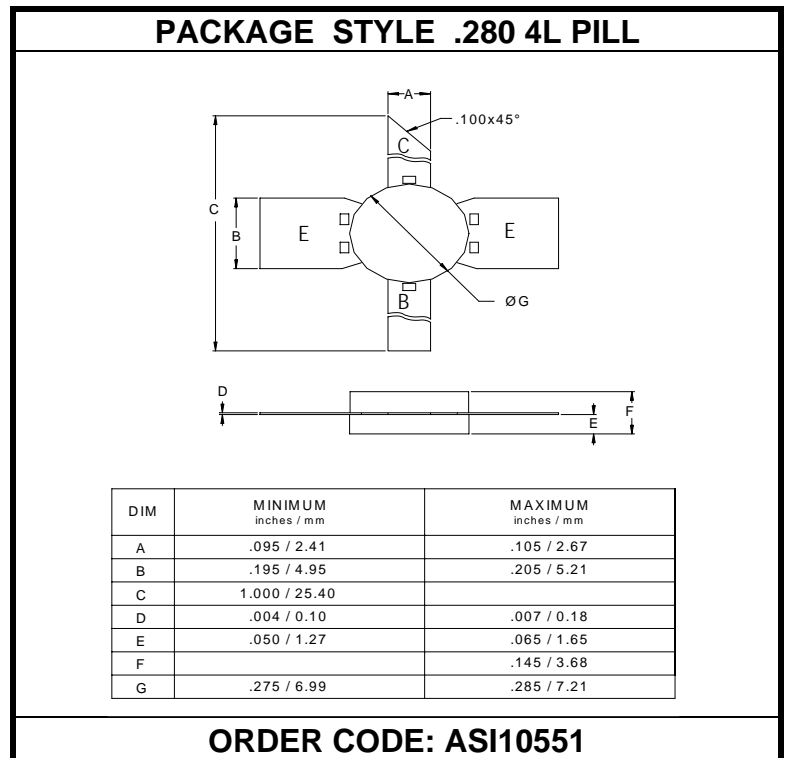
The **ASI AVD0.5P** is Designed for Class A, DME/TACAN Applications up to 1150 MHz.

FEATURES:

- Class A Operation
- $P_G = 10$ dB at 0.5 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	300 mA
V_{CE}	20 V
P_{DISS}	--- W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	35.0 °C/W


CHARACTERISTICS $T_C = 25\text{ °C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	50			V
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 28$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		120	---
P_G	$V_{CC} = 12.5$ V $P_{OUT} = 0.5$ W $f = 1025 - 1150$ MHz	10			dB